

## Silicon Power Schottky Diode

$V_{RRM} = 20\text{ V} - 100\text{ V}$

$I_F = 600\text{ A}$

### Features

- High Surge Capability
- Types up to 100 V  $V_{RRM}$

Twin Tower Package



Maximum ratings, at  $T_j = 25\text{ °C}$ , unless otherwise specified ("R" devices have leads reversed)

Parameter	Symbol	Conditions	MBR60020CT (R)	MBR60030CT (R)	MBR60035CT (R)	MBR60040CT (R)	Unit
Repetitive peak reverse voltage	$V_{RRM}$		20	30	35	40	V
RMS reverse voltage	$V_{RMS}$		14	21	25	28	V
DC blocking voltage	$V_{DC}$		20	30	35	40	V
Continuous forward current	$I_F$	$T_C \leq 100\text{ °C}$	600	600	600	600	A
Surge non-repetitive forward current, Half Sine Wave	$I_{F,SM}$	$T_C = 25\text{ °C}$ , $t_p = 8.3\text{ ms}$	4000	4000	4000	4000	A
Operating temperature	$T_j$		-40 to 150	-40 to 150	-40 to 150	-40 to 150	°C
Storage temperature	$T_{stg}$		-40 to 175	-40 to 175	-40 to 175	-40 to 175	°C

Electrical characteristics, at  $T_j = 25\text{ °C}$ , unless otherwise specified

Parameter	Symbol	Conditions	MBR60020CT (R)	MBR60030CT (R)	MBR60035CT (R)	MBR60040CT (R)	Unit
Diode forward voltage	$V_F$	$I_F = 300\text{ A}$ , $T_j = 25\text{ °C}$	0.75	0.75	0.75	0.75	V
Reverse current	$I_R$	$V_R = 20\text{ V}$ , $T_j = 25\text{ °C}$	1	1	1	1	mA
		$V_R = 20\text{ V}$ , $T_j = 125\text{ °C}$	20	20	20	20	

### Thermal characteristics

Thermal resistance, junction - case	$R_{thJC}$		0.12	0.12	0.12	0.12	°C/W
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Figure .1-Typical Forward Characteristics

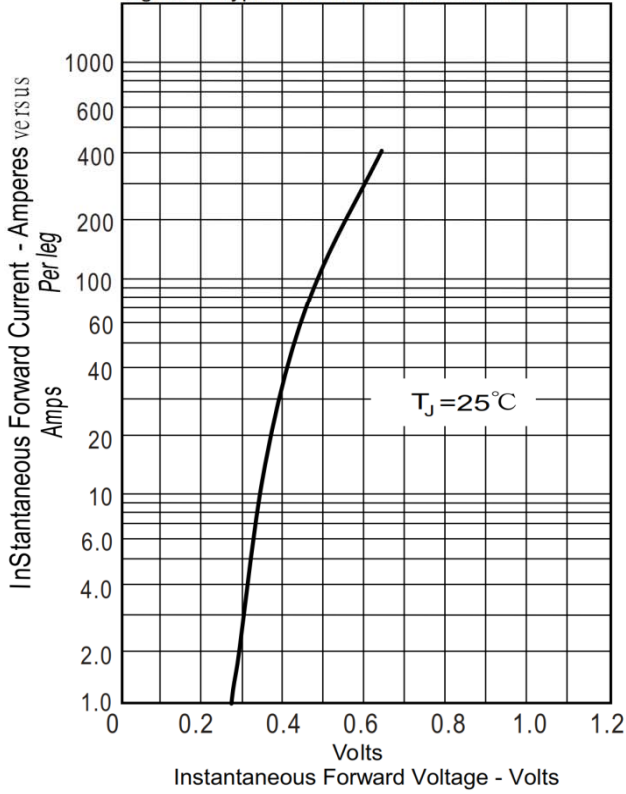


Figure .2- Forward Derating Curve

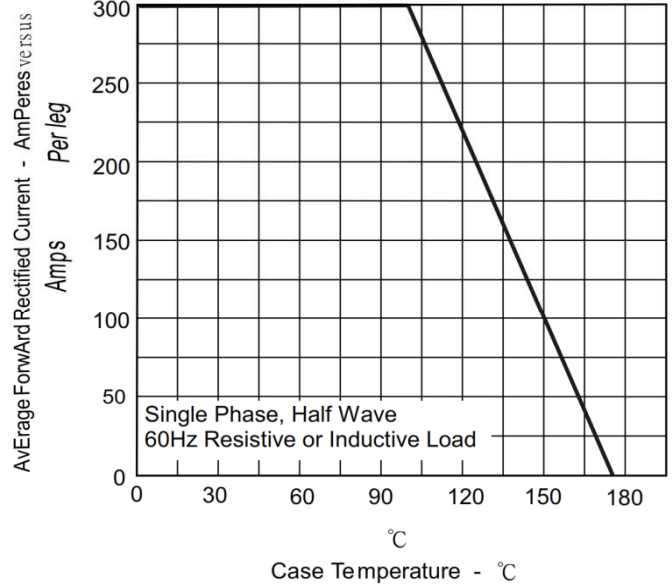


Figure .3- Peak Forward Surge Current

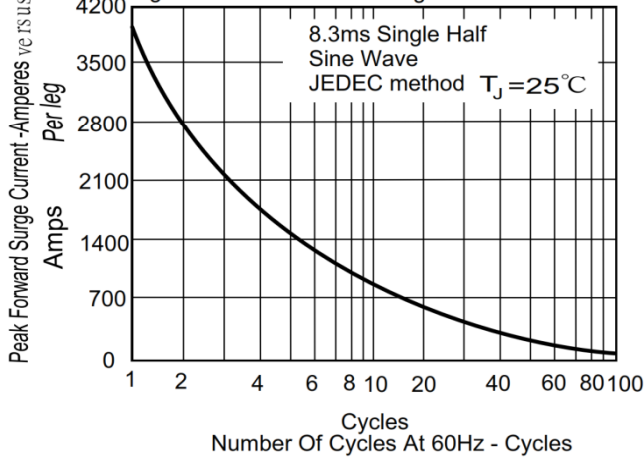


Figure .4-Typical Reverse Characteristics

